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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Ko, *et al.* Docket No.: TSM03-0615  
Serial No.: 10/729,095 Art Unit: 2818  
Filed: December 5, 2003 Examiner: TBD  
For: Structure And Method Of A Strained Channel Transistor And A Second  
Semiconductor Component In An Integrated Circuit

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Form PTO/SB/08A & 08B with 70 references cited (5 pages)  
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Respectfully submitted,

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Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

The Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A & 08B that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(3), before the mailing of a first Office action on the merits.

Pursuant to 37 CFR 1.98(a)(2)(i), as amended, copies of U.S. Patents cited are not being submitted. However, Applicant has included copies of any non-patent literature.

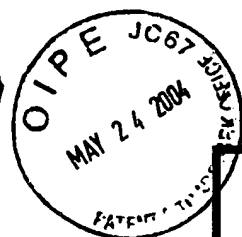
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PTO/SB/08A (02-03)

Approved for use through 4/30/2003. OMB 0651-0031

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Substitute for form 1449/PTO				<b>Complete if Known</b>	
				Application Number	10/729,095
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)				Filing Date	December 5, 2003
				First Named Inventor	Ko, et al.
				Art Unit	2818
				Examiner Name	TBD
Sheet	1	of	5	Attorney Docket Number	TSM03-0615

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
	1	US-4,314,269	02-02-1982	Fujiki	
	2	US-4,631,803	12-30-1986	Hunter, et al.	
	3	US-4,946,799	08-07-1990	Blake, et al.	
	4	US-5,447,884	09-05-1995	Fahey, et al.	
	5	US-5,461,250	10-24-1995	Burghartz, et al.	
	6	US-5,534,713	07-09-1996	Ismail, et al.	
	7	US-5,629,544	05-13-1997	Voldman, et al.	
	8	US-5,714,777	02-03-1998	Ismail, et al.	
	9	US-5,763,315	06-09-1998	Benedict, et al.	
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	17	US-6,258,664 B1	07-10-2001	Reinberg	
	18	US-6,291,321 B1	09-18-2001	Fitzgerald	
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	20	US-6,358,791 B1	03-19-2002	Hsu, et al.	
	21	US-6,387,739 B1	05-14-2002	Smith, III	
	22	US-2002/0076899 A1	06-20-2002	Skotnicki, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
	23	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation		

Examiner Signature		Date Considered	
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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(use as many sheets as necessary)*

Sheet	2	of	5
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**Complete if Known**

Application Number	10/729,095
Filing Date	December 5, 2003
First Named Inventor	Ko, <i>et al.</i>
Art Unit	2818
Examiner Name	TBD
Attorney Docket Number	TSM03-0615

## U.S. PATENT DOCUMENTS

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Substitute for form 1449B/PTO			<b>Complete if Known</b>		
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>			Application Number	10/729,095	
			Filing Date	December 5, 2003	
			First Named Inventor	Ko, <i>et al.</i>	
			Group Art Unit	2818	
			Examiner Name	TBD	
Sheet	3	of	5	Attorney Docket Number	TSM03-0615

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	40	ISMAIL, K., <i>et al.</i> , "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letters, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.	
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	42	GÁMIZ, F., <i>et al.</i> , "Strained-Si/SiGe-on-Insulator Inversion Layers: The Role of Strained-Si Layer Thickness on Electron Mobility," Applied Physics Letters, Vol. 80, No. 22, (June 3, 2002), pp. 4160-4162.	
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	51	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers – I. Misfit Dislocations," Journal of Crystal Growth, Vol. 27, (1974), pp. 118-125.	
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Examiner Signature			Date Considered

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				Filing Date	December 5, 2003
				First Named Inventor	Ko, <i>et al.</i>
				Group Art Unit	2818
				Examiner Name	TBD
Sheet	4	of	5	Attorney Docket Number	TSM03-0615

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
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	53	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers -- III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.	
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			Application Number	10729,095	
			Filing Date	December 5, 2003	
			First Named Inventor	Ko, <i>et al.</i>	
			Group Art Unit	2818	
			Examiner Name	TBD	
Sheet	5	of	5	Attorney Docket Number	TSM03-0615

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
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	66	CAVASSILAS, N., <i>et al.</i> , "Capacitance-Voltage Characteristics of Metal-Oxide-Strained Semiconductor Si/SiGe Heterostructures," Nanotech 2002, Vol. 1, pp. 600-603.	
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